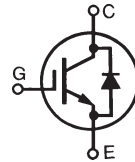


# High Voltage, High Frequency, BiMOSFET™ Monolithic Bipolar MOS Transistor

## IXBF16N360



$$V_{CES} = 3600V$$

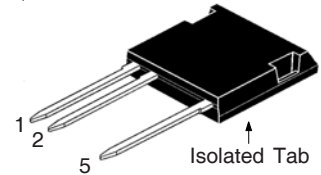
$$I_{C90} = 16A$$

$$V_{CE(sat)} \leq 3.0V$$

(Electrically Isolated Tab)

Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ C$ to $150^\circ C$	3600	V
$V_{CGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GE} = 1M\Omega$	3600	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ C$	26	A
$I_{C90}$	$T_C = 90^\circ C$	16	A
$I_{CM}$	$T_C = 25^\circ C$ , 1ms	72	A
<b>SSOA</b> <b>(RBSOA)</b>	$V_{GE} = 15V$ , $T_{VJ} = 125^\circ C$ , $R_G = 25\Omega$ Clamped Inductive Load	$I_{CM} = 60$ $V_{CES} \leq 1500$	A V
<b><math>T_{SC}</math></b> <b>(SCSOA)</b>	$V_{GE} = 15V$ , $T_J = 125^\circ C$ , $R_G = 82\Omega$ , $V_{CE} = 1500V$ , Non-Repetitive	10	$\mu s$
$P_C$	$T_C = 25^\circ C$	125	W
$T_J$		-55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		-55 ... +150	$^\circ C$
$T_L$	Maximum Lead Temperature for Soldering	300	$^\circ C$
$T_{SOLD}$	Plastic Body for 10s	260	$^\circ C$
$F_C$	Mounting Force with Clip	20..120 / 4.5..27	N/lb
$V_{ISOL}$	50/60Hz, 5 Seconds	4000	V~
<b>Weight</b>		8	g

### ISOPLUS i4-Pak™



1 = Gate  
2 = Emitter  
5 = Collector

### Features

- Silicon Chip on Direct-Copper Bond (DCB) Substrate
- Isolated Mounting Surface
- 4000V~ Electrical Isolation
- High Blocking Voltage
- High Frequency Operation

### Advantages

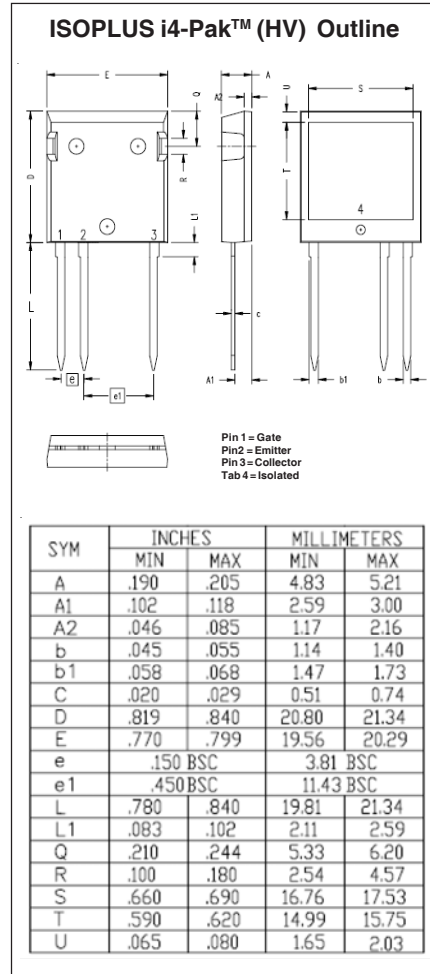
- Low Gate Drive Requirement
- High Power Density

### Applications

- Switch-Mode and Resonant-Mode Power Supplies
- Uninterruptible Power Supplies (UPS)
- Laser Generators
- Capacitor Discharge Circuits
- AC Switches

Symbol	Test Conditions ( $T_J = 25^\circ C$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{CES}$	$I_C = 250\mu A$ , $V_{GE} = 0V$	3600		V
$V_{GE(th)}$	$I_C = 250\mu A$ , $V_{CE} = V_{GE}$	3.0		5.0 V
$I_{CES}$	$V_{CE} = V_{CES}$ , $V_{GE} = 0V$ Note 2, $T_J = 125^\circ C$			25 $\mu A$ 1 mA
$I_{GES}$	$V_{CE} = 0V$ , $V_{GE} = \pm 20V$			$\pm 200$ nA
$V_{CE(SAT)}$	$I_C = 16A$ , $V_{GE} = 15V$ , Note 1 $T_J = 125^\circ C$		2.5 3.1	V V

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$I_C = 16\text{A}, V_{CE} = 20\text{V}$ , Note 1	7	12	S
$C_{ies}$	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		1116	pF
$C_{oes}$			60	pF
$C_{res}$			25	pF
$Q_{g(on)}$	$I_C = 16\text{A}, V_{GE} = 15\text{V}, V_{CE} = 1.5\text{KV}$		65	nC
$Q_{ge}$			7	nC
$Q_{gc}$			30	nC
$t_{d(on)}$	<b>Resistive load, <math>T_J = 25^\circ\text{C}</math></b>		30	ns
$t_r$		$I_C = 16\text{A}, V_{GE} = 15\text{V}$	260	ns
$t_{d(off)}$	$V_{CE} = 1.5\text{KV}, R_G = 25\Omega$		184	ns
$t_f$			110	ns
$t_{d(on)}$	<b>Resistive load, <math>T_J = 125^\circ\text{C}</math></b>		36	ns
$t_r$		$I_C = 16\text{A}, V_{GE} = 15\text{V}$	385	ns
$t_{d(off)}$	$V_{CE} = 1.5\text{KV}, R_G = 25\Omega$		190	ns
$t_f$			115	ns
$R_{thJC}$				1.0 $^\circ\text{C/W}$
$R_{thCS}$		0.15		$^\circ\text{C/W}$



## Reverse Diode

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max
$V_F$	$I_F = 16\text{A}, V_{GE} = 0\text{V}$ , Note 1			3.5 V
$t_{rr}$	$I_F = 16\text{A}, V_{GE} = 0\text{V}, -di_F/dt = 100\text{A}/\mu\text{s}$		620	ns
$I_{RM}$		$V_R = 100\text{V}, V_{GE} = 0\text{V}$		21.5
$Q_{RM}$			6.7	$\mu\text{C}$

## Notes:

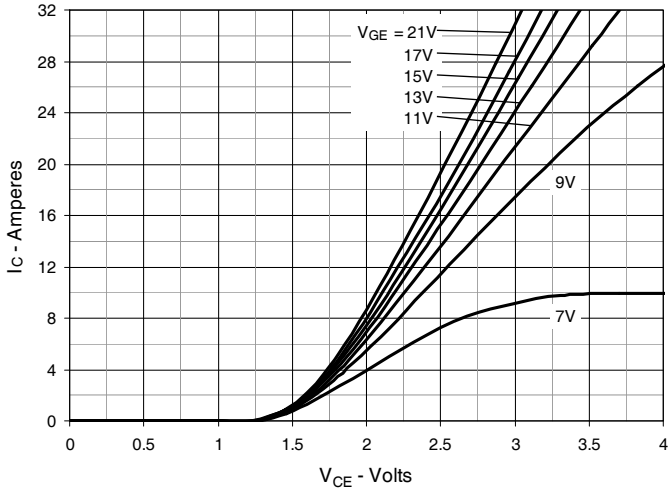
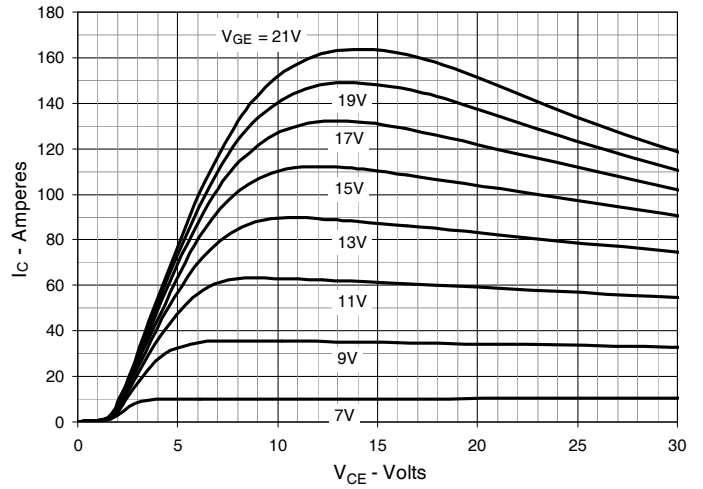
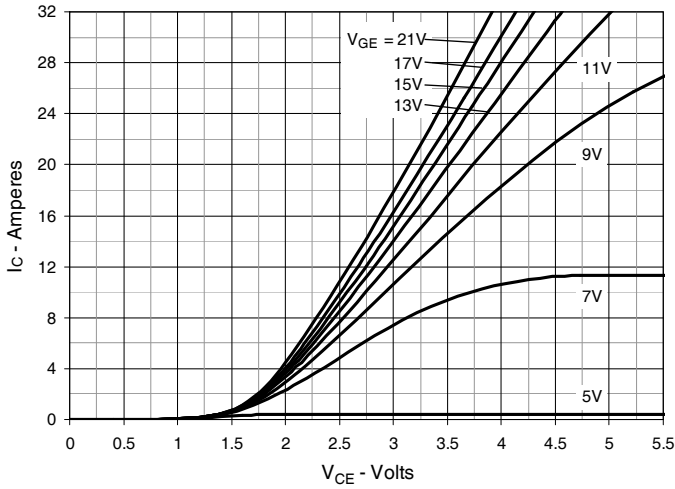
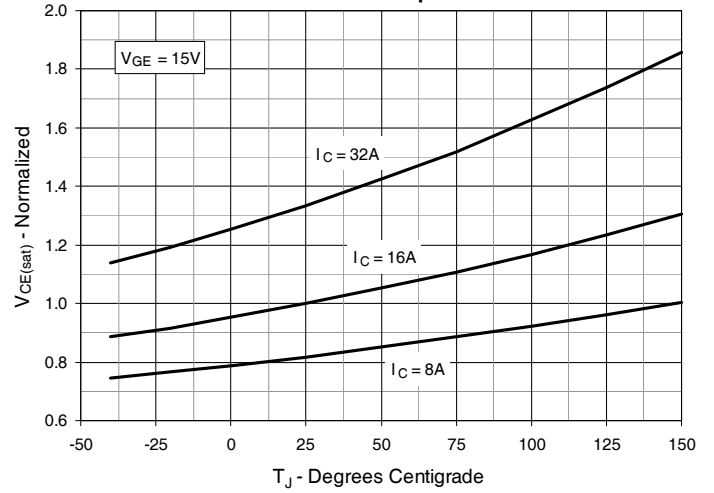
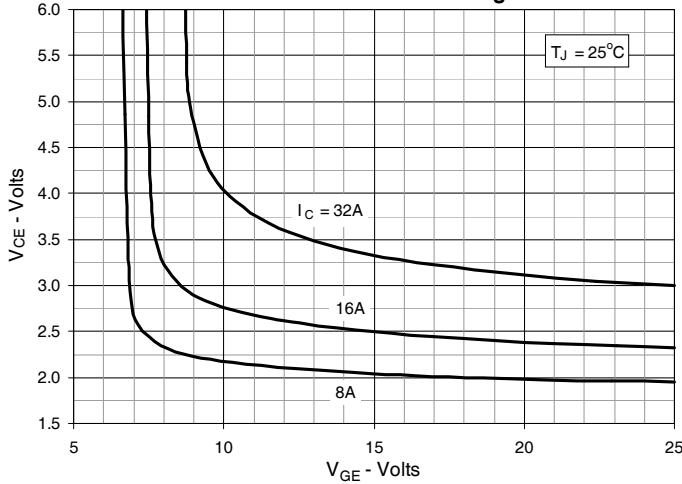
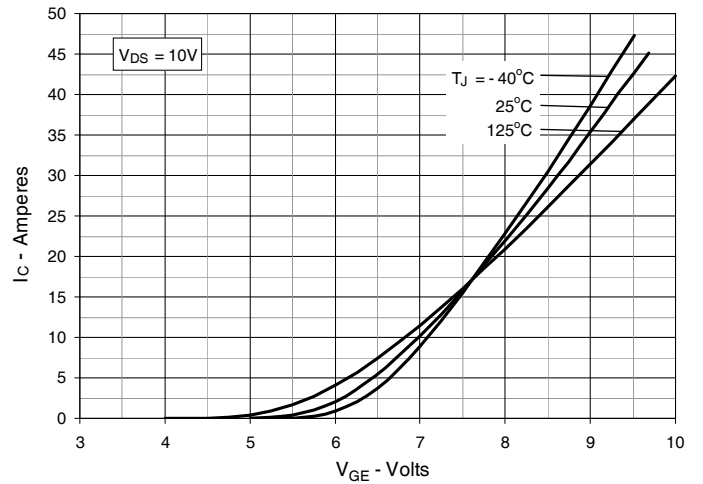
1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .
2. Device must be heatsunk for high-temperature leakage current measurements to avoid thermal runaway.

### ADVANCE TECHNICAL INFORMATION

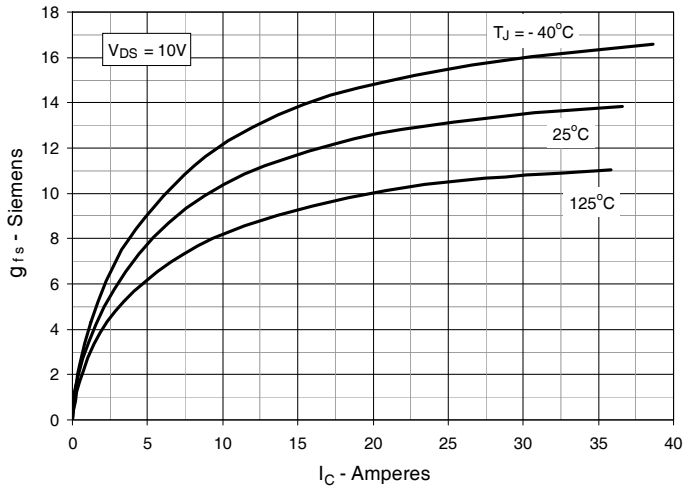
The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions and Dimensions.

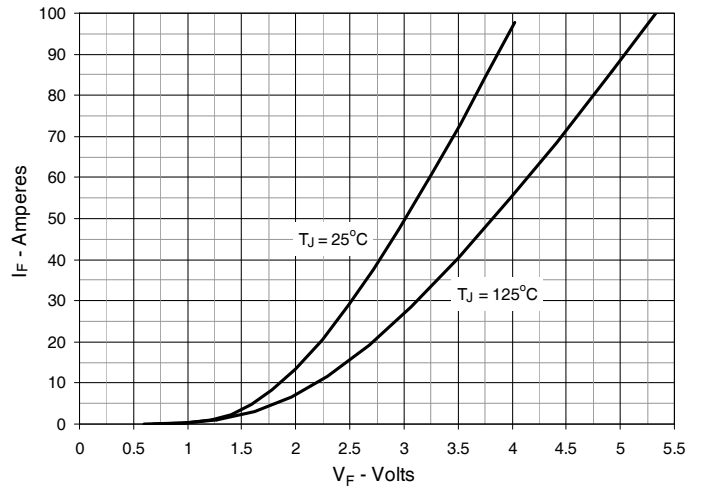
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$** 

**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$** 

**Fig. 3. Output Characteristics @  $T_J = 125^\circ\text{C}$** 

**Fig. 4. Dependence of  $V_{CE(sat)}$  on Junction Temperature**

**Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage**

**Fig. 6. Input Admittance**


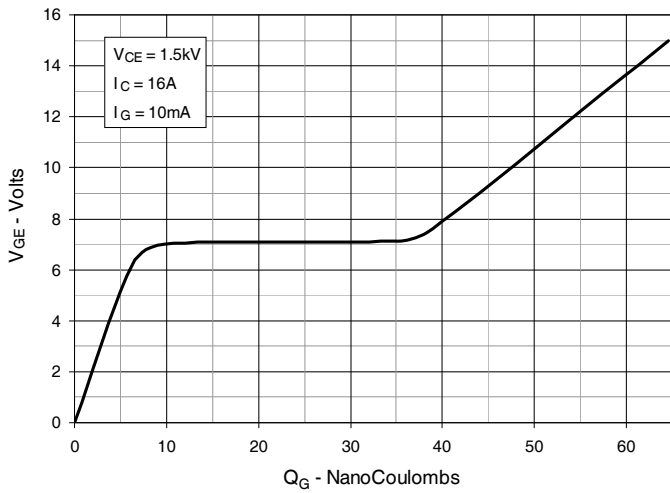
**Fig. 7. Transconductance**



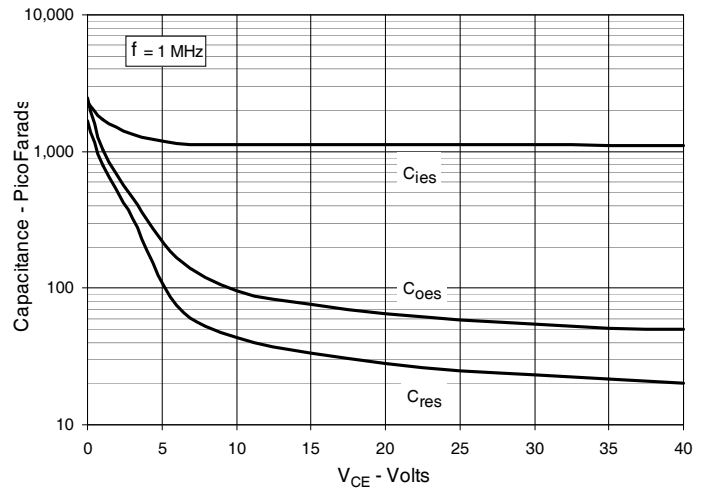
**Fig. 8. Forward Voltage Drop of Intrinsic Diode**



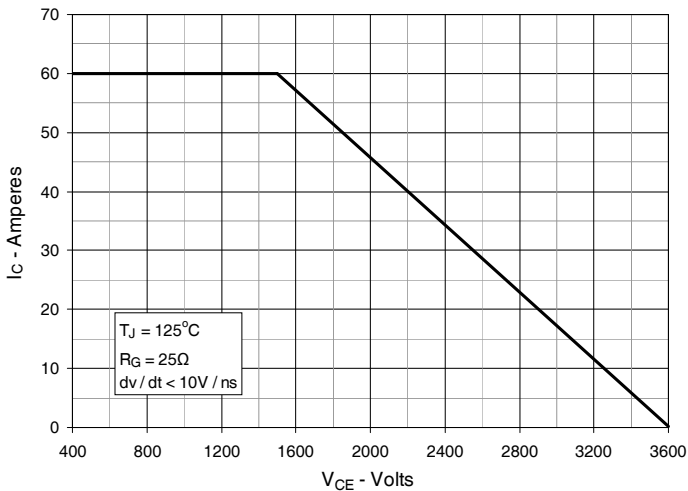
**Fig. 9. Gate Charge**



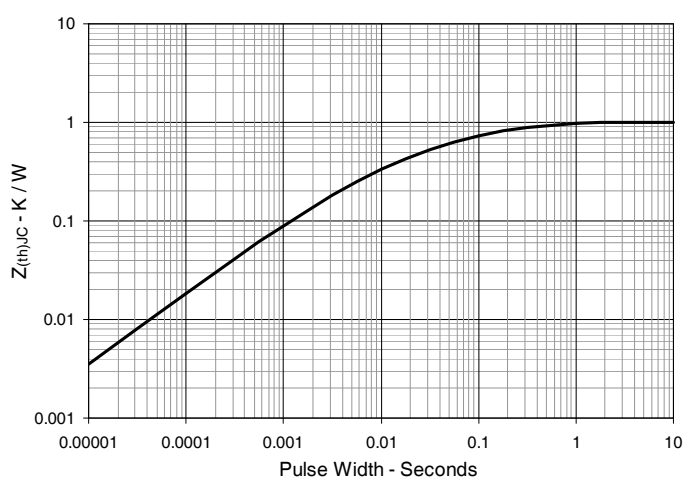
**Fig. 10. Capacitance**

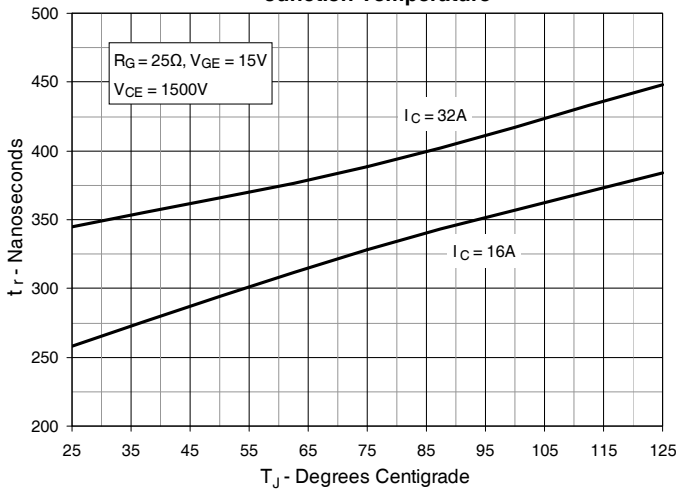
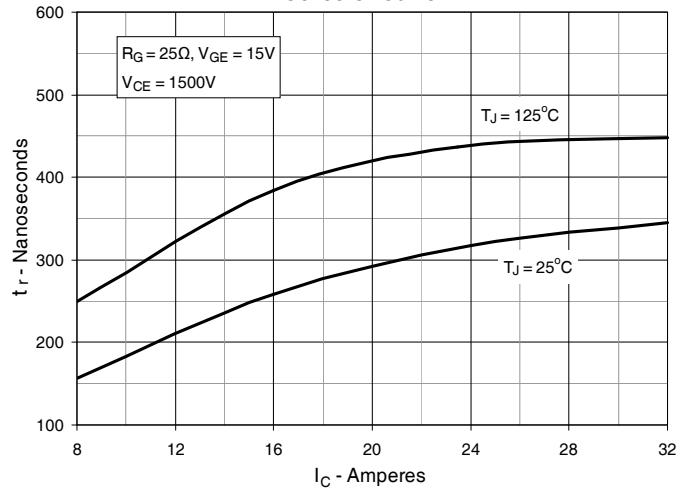
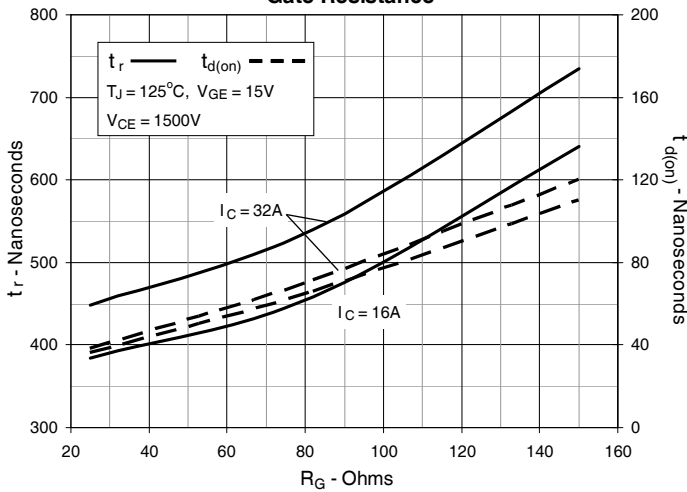
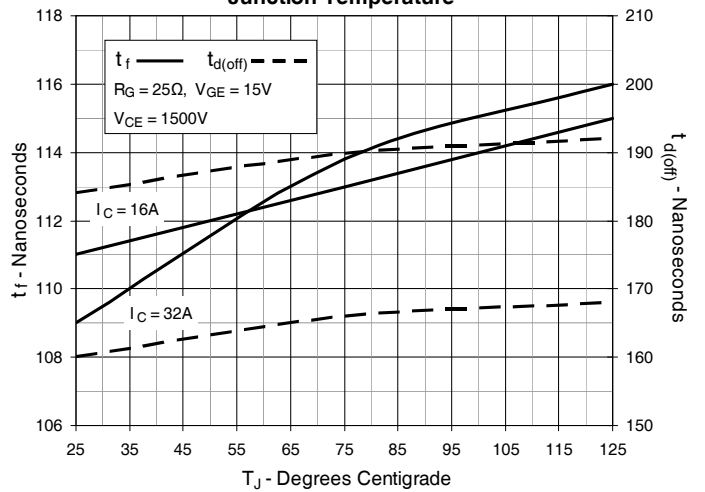
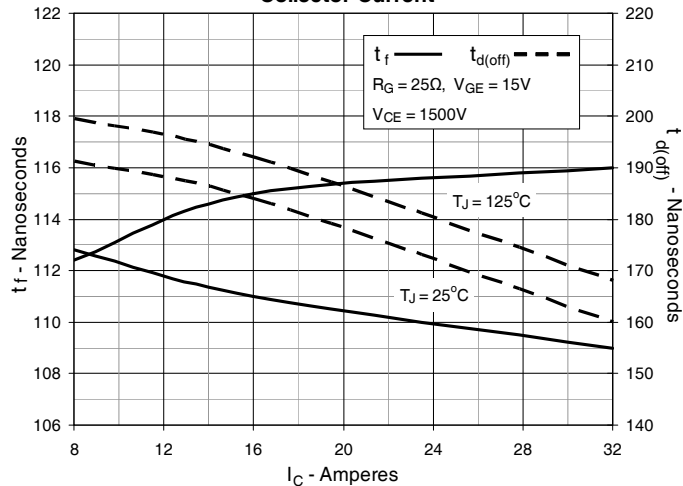
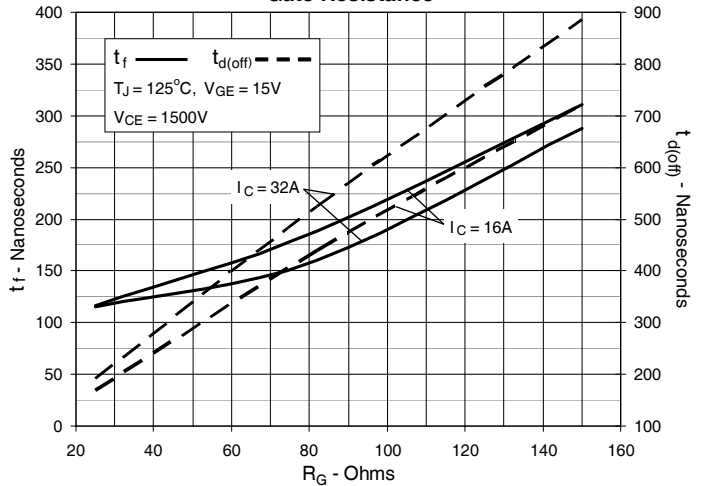


**Fig. 11. Reverse-Bias Safe Operating Area**

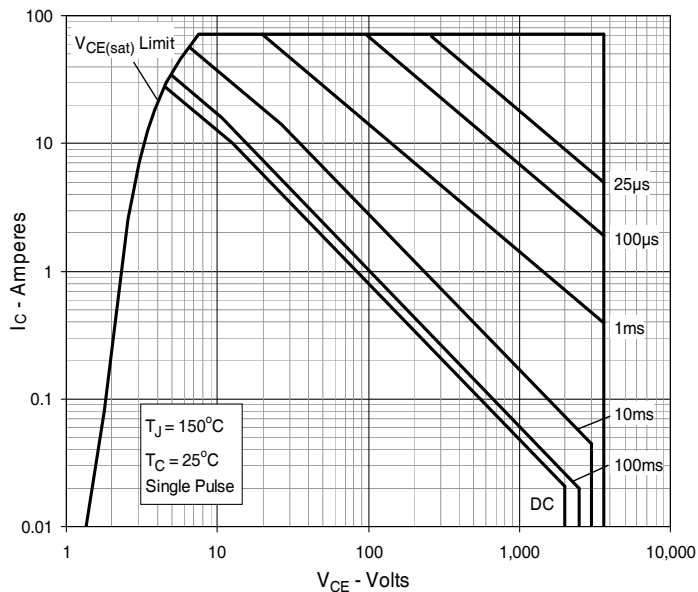


**Fig. 12. Maximum Transient Thermal Impedance**

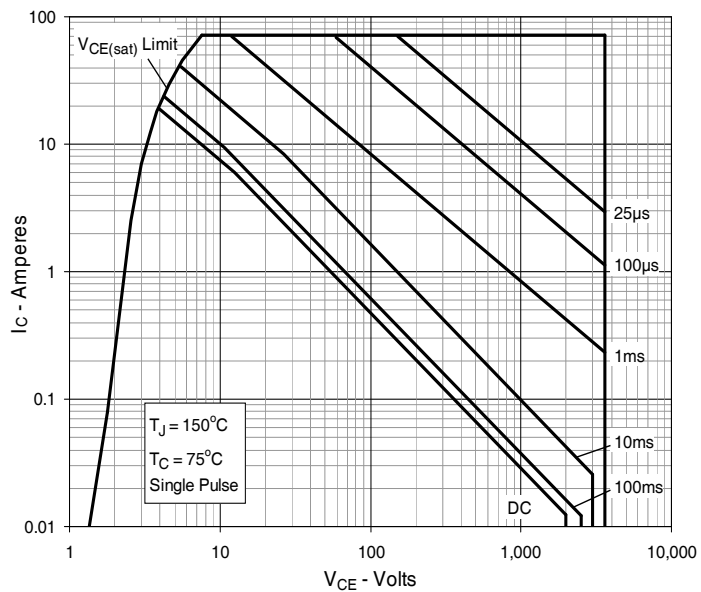


**Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature**

**Fig. 14. Resistive Turn-on Rise Time vs. Collector Current**

**Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance**

**Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature**

**Fig. 17. Resistive Turn-off Switching Times vs. Collector Current**

**Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance**


**Fig. 19. Forward-Bias Safe Operating Area @  $T_C = 25^\circ\text{C}$**



**Fig. 20. Forward-Bias Safe Operating Area @  $T_C = 75^\circ\text{C}$**





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